

In the Specification

Please replace the heading beginning on Page 1, line 1 with the following headings:

--BACKGROUND OF THE INVENTION

Field of the Invention--

Please replace the heading before the paragraph on Page 1, line 8 with the following heading:

--DESCRIPTION OF RELATED ART--

Please replace the heading before the paragraph on Page 3, line 17 with the following heading:

--SUMMARY OF THE INVENTION--

Please replace the heading before the paragraph on Page 13, line 3 with the following heading:

--DETAILED DESCRIPTION OF THE PREFERRED EMBODIMENTS--

Please replace the paragraph beginning on page 17, line 12 with the following rewritten paragraph:

--As shown in Fig. 3, a large number of circuits 10 for the IC element are formed with equidistance in an inner portion exclusive of the outermost peripheral portion, wherein the surface passivation film 2 is formed over the surface on which the circuit for the IC element are formed (see Figs. 4 and 5).--

Please replace the paragraph beginning on page 17, line 19 with the following rewritten paragraph:

--In the IC element manufacturing method according to a first exemplary embodiment shown in Figs. 4A, 4B, 4C, 4D, 4E and 4F, the metal-sputtered layer or alternatively metal-evaporated layer 6 is formed uniformly on the surface passivation film 2 deposited on the circuit-formed surface of the finished wafer 11 by using aluminum or an aluminum alloy or alternatively copper or a copper alloy, as shown in Fig. 4A. Subsequently, a photoresist layer 12 is uniformly formed on the metal-sputtered layer or alternatively metal-evaporated layer 6 and then the photoresist layer as formed is covered with a mask 13 of a required pattern inclusive of the coils, whereon the photoresist layer 12 is exposed to illumination of light rays 14 of a predetermined wavelength externally of the mask 13, as is shown in Fig. 4B. Thereafter, the photoresist layer 12 undergone the light exposure is subjected to a developing process, whereby the light-exposed portions of the photoresist layer 12 are removed, as a result of which the portions of the metal-sputtered layer or alternatively metal-evaporated layer 6 which correspond to the above-mentioned light exposure pattern is exposed outwardly, as is shown in Fig. 4C. The exposure pattern of the metal-sputtered layer or alternatively metal-evaporated layer 6 includes a ring-shaped electrode portion 15, the antenna coils 3 formed on the portions opposite to the aforementioned circuits 12, respectively, and lead portions 16 for connecting the individual antenna coils 3 and the electrode portion 15, as is shown in Fig. 6. In succession, by making use of the above-mentioned electrode portion 15 as one electrode, electroplating or precision electroforming process is performed on the exposed portions of the metal-sputtered layer or alternatively metal-evaporated layer 6, or thereby laminate the metal-plated layers 7 on the

exposed portions of the metal-sputtered layer or alternatively metal-evaporated layer 6, as shown in Fig. 4D. Subsequently, the photoresist layer 12 deposited on the surface of the finished wafer 11 is removed through an ashing or the like process to thereby obtain the finished wafer 11 formed with the metal-plated 7 including the electrode portion 15, the antenna coils 3 and the lead portions 16 deposited on the uniform metal-sputtered layer on alternatively metal-evaporated layer 6, as shown in Fig. 4E. In succession, the metal-sputtered layer or alternatively metal-evaporated layer 6 exposed through the metal-plated layer 7 is selectively etched to thereby remove the metal-sputtered layer or alternatively metal-evaporated layer 6 exposed externally through the metal-plated layer 7, as is shown in Fig. 4F. Thus, there is obtained the finished wafer 11 on which both the metal-sputtered layer or alternatively metal-evaporated layer 6 and the metal plated layer 7 are formed in the required conductive pattern shown in Fig. 6. Finally, the finished after 11 mentioned just above is scribed to obtain the desired IC elements 1 shown in Fig. 1.--

In the Claims

Please cancel claims 7, 8 and 20-27 without prejudice or disclaimer of the subject matter contained therein.

Please amend the claims as follows:

sub C

1. (Amended) An IC element formed integrally with a coil for performing contactless data communication with external equipment, comprising:
a conductor constituting said coil implemented in a multilayer structure including a metal-sputtered layer or alternatively a metal-evaporated-layer and a metal-plated layer.